

PLUS Search Results for S/N 10/002,696, Searched July 10, 2002 (Top 50)

4577215	5879992	5523980	6034892	4884239
5266509	5978272	5598367	6125053	4903097
4357685	6046086	5687115	6144581	4994403
5287536	6229176	5694356	6177315	5010028
5414287	4442447	5751635	6212100	5182726
6191444	4820941	5790460	6212100	5218569
4597000	4868790	5801993	6240015	5317532
5187683	5265052	5859454	4513397	5384743
5216269	5371031	5898613	4592130	5387534
5694445	5523249	5932908	4618876	5394362

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/002,696 on July 10, 2002

Combined Classifications

12 365/185.18
9 257/315
9 365/185.03
9 365/185.29
8 365/185.22
7 365/185.14
7 365/185.26
6 365/185.2
6 365/185 21
6 365/185 28
5 365/185 01
5 365/185.19
5 365/185 33
4 257/316
4 257/321
4 257/324
4 365/185 23
4 365/185 27
4 365/218
4 438/264
4 438/594
3 257/314
3 365/149
3 365/185 06
3 365/185 1
3 365/185 11
3 365/185 16
3 365/226
3 438/261
3 438/263
2 257/318
2 257/320
2 257/322
2 365/185 02
2 365/185.24
2 365/185.25
2 365/185.3
2 365/185.31
2 365/189 09
2 365/230 06
2 438/266
2 438/279

- 12 365/185.18 (0 OR, 12 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
365/185.18 ..Particular biasing
- 9 257/315 (2 OR, 7 XR)
Class 257 ACTIVE SOLID-STATE DEVICES
257/213 FIELD EFFECT DEVICE
257/288 ..Having insulated electrode (e.g., MOSFET, MOS diode)
257/314 ..Variable threshold (e.g., floating gate memory device)
257/315 ...With floating gate electrode
- 9 365/185.03 (6 OR, 3 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
365/185.03 ..Multiple values (e.g., analog)
- 9 365/185.29 (2 OR, 7 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
365/185.18 ..Particular biasing
365/185.29 ..Erase
- 8 365/185.22 (0 OR, 8 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
365/185.18 ..Particular biasing
365/185.2 ..Reference signal (e.g., dummy cell)
365/185.22 ...Verify signal
- 7 365/185.14 (4 OR, 3 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
365/185.05 ..Particular connection
365/185.14 ..Program gate
- 7 365/185.26 (0 OR, 7 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
365/185.18 ..Particular biasing
365/185.26 ..Floating electrode (e.g., source, controlgate, drain)
- 6 365/185.2 (0 OR, 6 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
365/185.18 ..Particular biasing
365/185.2 ..Reference signal (e.g., dummy cell)
- 6 365/185.21 (2 OR, 4 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/185.01 FLOATING GATE
365/185.18 ..Particular biasing
365/185.2 ..Reference signal (e.g., dummy cell)
365/185.21 ...Sensing circuitry (e.g., current mirror)

6 365/185.28 (1 OR, 5 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185 01 FLOATING GATE

365/185 18 Particular biasing

365/185 28 Tunnel programming

5 365/185.01 (0 OR, 5 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185 01 FLOATING GATE

5 365/185.19 (2 OR, 3 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185 01 FLOATING GATE

365/185 18 Particular biasing

365/185 19 Multiple pulses (e.g., ramp)

5 365/185.33 (0 OR, 5 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185 01 FLOATING GATE

365/185 18 Particular biasing

365/185 29 Erase

365/185 33 ..Flash

4 257/316 (3 OR, 1 XR)

Class 257 ACTIVE SOLID-STATE DEVICES

257/213 FIELD EFFECT DEVICE

257/288 Having insulated electrode (e.g., MOSFET, MOS diode)

257/314 Variable threshold (e.g., floating gate memory device)

257/315 ..With floating gate electrode

257/316 ..With additional contacted control electrode

4 257/321 (1 OR, 3 XR)

Class 257 ACTIVE SOLID-STATE DEVICES

257/213 FIELD EFFECT DEVICE

257/288 Having insulated electrode (e.g., MOSFET, MOS diode)

257/314 Variable threshold (e.g., floating gate memory device)

257/315 ...With floating gate electrode

257/316 ...With additional contacted control electrode

257/321With thin insulator region for charging or discharging floating electrode by quantum mechanical tunneling

4 257/324 (0 OR, 4 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/213 FIELD EFFECT DEVICE

257/288 Having insulated electrode (e.g., MOSFET, MOS diode)

257/314 . Variable threshold (e.g., floating gate memory device)

257/324 ...Multiple insulator layers (e.g., MNOS structure)